CD4013BMS

December 1992

CMOS Dual 'D'-Type Flip-Flop

Features

- **High-Voltage Type (20V Rating)**
- **Set-Reset Capability**
- **Static Flip-Flop Operation - Retains State Indefinitely With Clock Level Either "High" Or "Low"**
- **Medium-Speed Operation - 16 MHz (typ.) Clock Toggle Rate at 10V**
- **Standardized Symmetrical Output Characteristics**
- **100% Tested for Quiescent Current at 20V**
- **Maximum Input Current of 1μA at 18V Over Full Package Temperature Range; 100nA at 18V and +25°C**
- **Noise Margin (Over Full Package Temperature Range):**
  - **1V at VDD = 5V**
  - **2V at VDD = 10V**
  - **2.5V at VDD = 15V**
- **5V, 10V and 15V Parametric Ratings**
- **Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"**

Applications

- **Registers**
- **Counters**
- **Control Circuits**

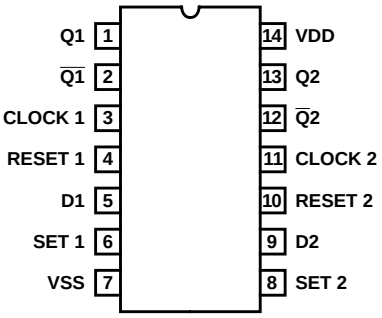
Description

CD4013BMS consists of two identical, independent data type flip-flops. Each flip-flop has independent data, set, reset, and clock inputs and Q and $\overline{Q}$ outputs. These devices can be used for shift register applications, and, by connecting $\overline{Q}$ output to the data input, for counter and toggle applications. The logic level present at the D input is transferred to the Q output during the positive going transition of the clock pulse. Setting or resetting is independent of the clock and is accomplished by a high level on the set or reset line, respectively.

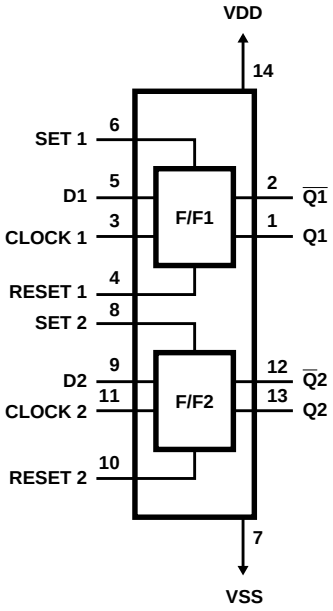
The CD4013BMS is supplied in these 14 lead outline packages:

Braze Seal DIP	H4Q
Frit Seal DIP	H1B
Ceramic Flatpack	H3W

Pinout



Functional Diagram



Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) . . . . . -0.5V to +20V
(Voltage Referenced to VSS Terminals)
Input Voltage Range, All Inputs . . . . . -0.5V to VDD +0.5V
DC Input Current, Any One Input. . . . . ±10mA
Operating Temperature Range . . . . . -55°C to +125°C
Package Types D, F, K, H
Storage Temperature Range (TSTG) . . . . . -65°C to +150°C
Lead Temperature (During Soldering) . . . . . +265°C
At Distance 1/16 ± 1/32 Inch (1.59mm ± 0.79mm) from case for 10s Maximum

Reliability Information

Thermal Resistance	θ_{ja}	θ_{jc}
Ceramic DIP and FRIT Package	80°C/W	20°C/W
Flatpack Package	70°C/W	20°C/W

Maximum Package Power Dissipation (PD) at +125°C
For TA = -55°C to +100°C (Package Type D, F, K) 500mW
For TA = +100°C to +125°C (Package Type D, F, K) . . . . . Derate Linearity at 12mW/°C to 200mW
Device Dissipation per Output Transistor 100mW
For TA = Full Package Temperature Range (All Packages Types)
Junction Temperature . . . . . +175°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)		GROUP A SUBGROUPS	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND		1	+25°C	-	2	µA
				2	+125°C	-	200	µA
		VDD = 18V, VIN = VDD or GND		3	-55°C	-	2	µA
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load		1, 2, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)		1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V		1	+25°C	0.53	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V		1	+25°C	1.4	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V		1	+25°C	3.5	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V		1	+25°C	-	-1.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V		1	+25°C	-	-1.4	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V		1	+25°C	-	-3.5	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA		1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10µA		1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VDD or GND		7	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 20V, VIN = VDD or GND		7	+25°C			
		VDD = 18V, VIN = VDD or GND		8A	+125°C			
		VDD = 3V, VIN = VDD or GND		8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	11	-	V

NOTES: 1. All voltages referenced to device GND, 100% testing being implemented.
2. Go/No Go test with limits applied to inputs
3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Propagation Delay Clock to Q, $\overline{Q}$	TPHL1 TPLH1	VDD = 5V, VIN = VDD or GND	9	+25°C	-	300	ns
			10, 11	+125°C, -55°C	-	405	ns
Propagation Delay Set to $\overline{Q}$, Reset to Q	TPHL2	VDD = 5V, VIN = VDD or GND	9	+25°C	-	400	ns
			10, 11	+125°C, -55°C	-	540	ns
Propagation Delay Set to Q, Reset to $\overline{Q}$	TPLH2	VDD = 5V, VIN = VDD or GND	9	+25°C	-	300	ns
			10, 11	+125°C, -55°C	-	405	ns
Transition Time Clock to Q, $\overline{Q}$	TTHL TTLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
			10, 11	+125°C, -55°C	-	270	ns
Maximum Clock Input Frequency	FCL	VDD = 5V, VIN = VDD or GND	9	+25°C	3.5	-	MHz
			10, 11	+125°C, -55°C	3.5/1.35	-	MHz

NOTES:

1. VDD = 5V, CL = 50pF, RL = 200K
2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	1.0	µA
				+125°C	-	30	µA
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2.0	µA
				+125°C	-	60	µA
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2.0	µA
				+125°C	-	120	µA
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-4.2	mA

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Output Current (Source)	IOH15	VDD =15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	+7	-	V
Propagation Delay Clock to Q, $\overline{Q}$	TPHL1 TPLH1	VDD = 10V	1, 2, 3	+25°C	-	130	ns
		VDD = 15V	1, 2, 3	+25°C	-	90	ns
Propagation Delay Set to $\overline{Q}$ Reset to Q	TPHL2	VDD = 10V	1, 2, 3	+25°C	-	170	ns
		VDD = 15V	1, 2, 3	+25°C	-	120	ns
Propagation Delay Set to Q Reset to $\overline{Q}$	TPLH2	VDD = 10V	1, 2, 3	+25°C	-	130	ns
		VDD = 15V	1, 2, 3	+25°C	-	90	ns
Transition Time Clock to Q, $\overline{Q}$	TTHL TTLH	VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Maximum Clock Input Frequency	FCL	VDD = 10V	1, 2, 3	+25°C	8	-	MHz
		VDD = 15V	1, 2, 3	+25°C	12	-	MHz
Minimum Data Setup Time	TS	VDD = 5V	1, 2, 3	+25°C	-	40	ns
		VDD = 10V	1, 2, 3	+25°C	-	20	ns
		VDD = 15V	1, 2, 3	+25°C	-	15	ns
Minimum Clock Pulse Width	TW	VDD = 5V	1, 2, 3	+25°C	-	140	ns
		VDD = 10V	1, 2, 3	+25°C	-	60	ns
		VDD = 15V	1, 2, 3	+25°C	-	40	ns
Minimum Set or Reset Pulse Width	TW	VDD = 5V	2, 3	+25°C	-	180	ns
		VDD = 10V	2, 3	+25°C	-	80	ns
		VDD = 15V	2, 3	+25°C	-	50	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7.5	pF

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	7.5	µA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA	1, 4	+25°C	-2.8	-0.2	V

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
N Threshold Voltage Delta	ΔVNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVPTH	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 3V, VIN = VDD or GND					
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.
2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
3. See Table 2 for +25°C limit.
4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-1	IDD	± 0.2μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1. 5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

CONFORMANCE GROUPS	MIL-STD-883 METHOD	TEST		READ AND RECORD	
		PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	OSCILLATOR	
					50kHz	25kHz
Static Burn-In 1 (Note 1)	1, 2, 12, 13	3-11	14			
Static Burn-In 2 (Note 1)	1, 2, 12, 13	7	3-6, 8-11, 14			
Dynamic Burn-In (Note 1)	-	4, 6-8, 10	14	1, 2, 12, 13	3, 11	5, 9
Irradiation (Note 2)	1, 2, 12, 13	7	3-6, 8-11, 14			

NOTE:

1. Each pin except VDD and GND will have a series resistor of 10K ± 5%, VDD = 18V ± 0.5V
2. Each pin except VDD and GND will have a series resistor of 47K ± 5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = 10V ± 0.5V

Logic Diagram

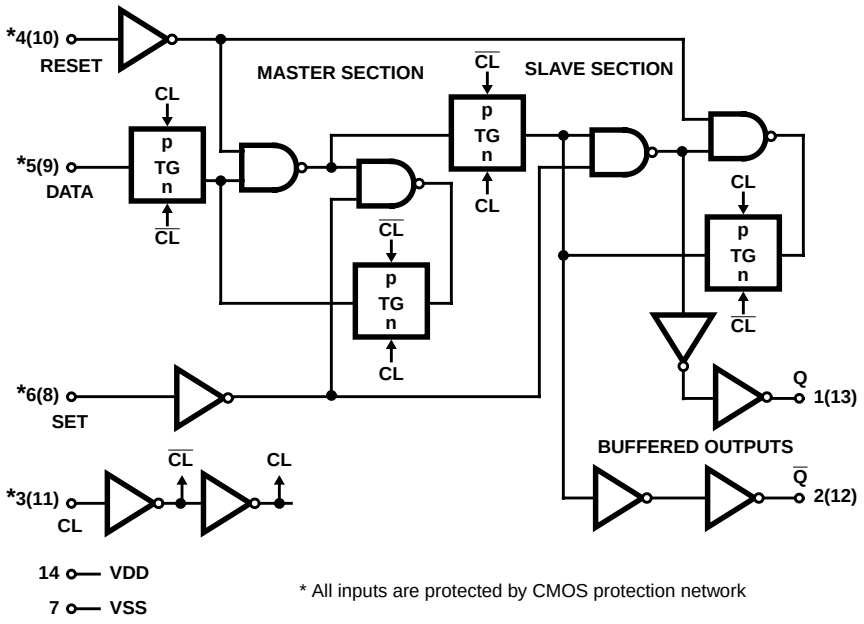


FIGURE 1. ONE OF TWO IDENTICAL FLIP-FLOPS

TRUTH TABLE

CL*	D	R	S	Q	$\overline{Q}$	
↑	0	0	0	0	1	
↑	1	0	0	1	0	
↓	X	0	0	Q	$\overline{Q}$	No Change
X	X	1	0	0	1	
X	X	0	1	1	0	
X	X	1	1	1	1	

Logic 0 = Low
Logic 1 = High
* = Level change
X = Don't care

N(N) = FF1/FF2 terminal assignments

Typical Performance Characteristics

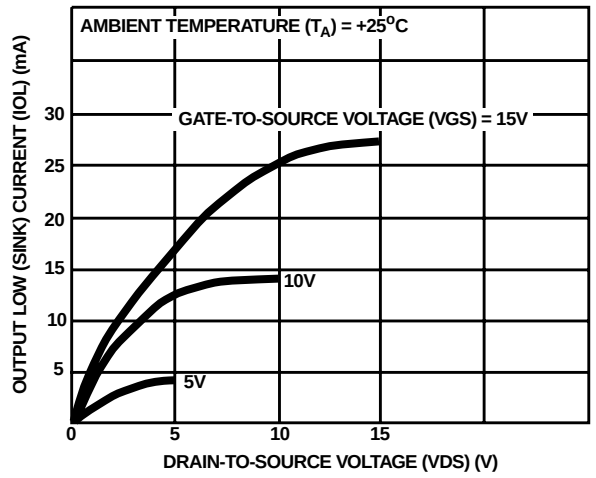


FIGURE 2. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

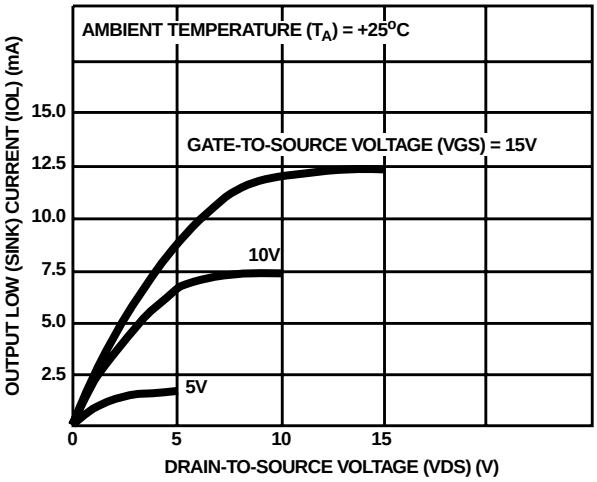


FIGURE 3. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

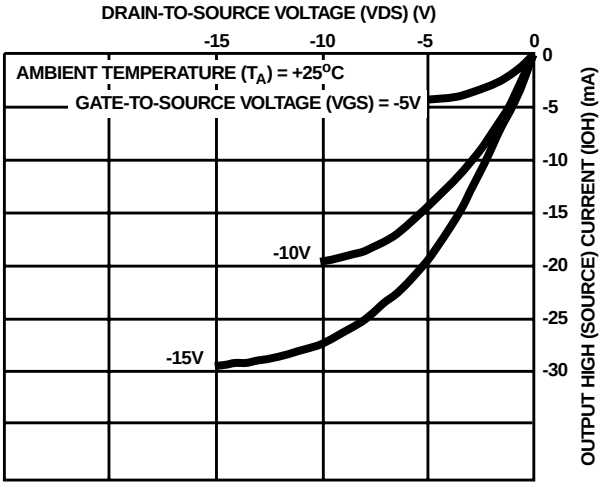


FIGURE 4. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

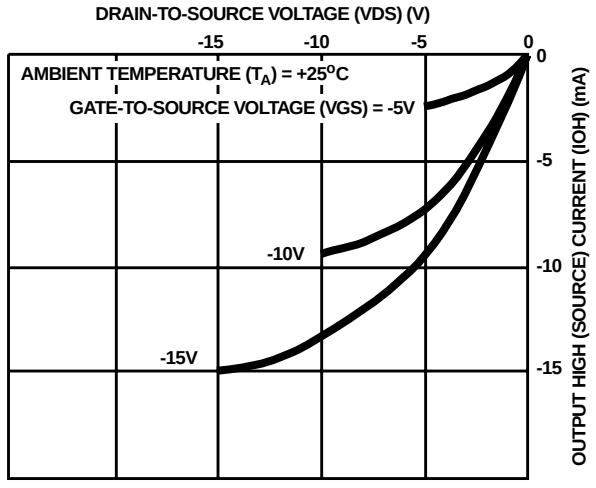


FIGURE 5. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

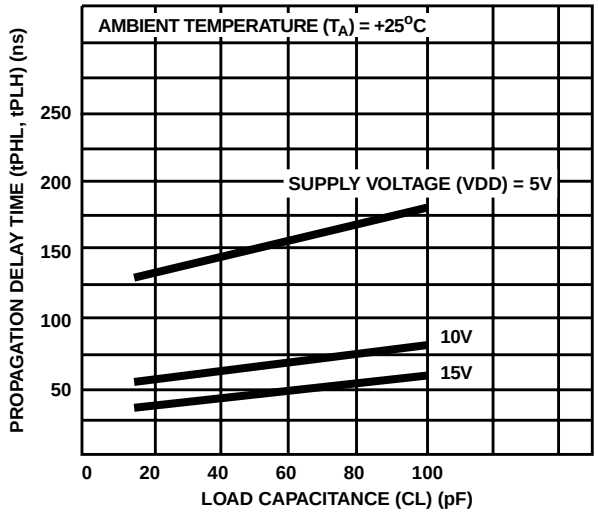


FIGURE 6. TYPICAL PROPAGATION DELAY TIME vs LOAD CAPACITANCE (CLOCK OR SET TO Q, CLOCK OR RESET TO $\overline{Q}$)

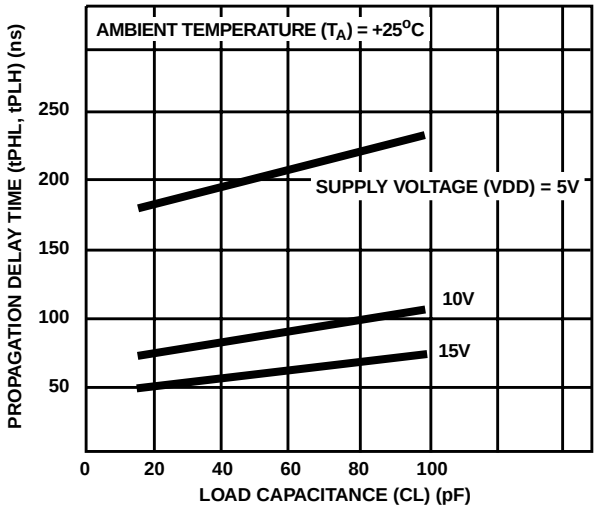


FIGURE 7. TYPICAL PROPAGATION DELAY TIME vs LOAD CAPACITANCE (SET TO $\overline{Q}$ OR RESET TO Q)

Typical Performance Characteristics (Continued)

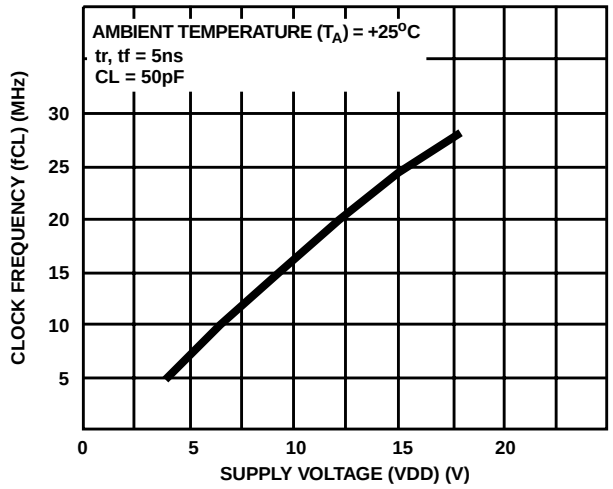


FIGURE 8. TYPICAL MAXIMUM CLOCK FREQUENCY vs SUPPLY VOLTAGE

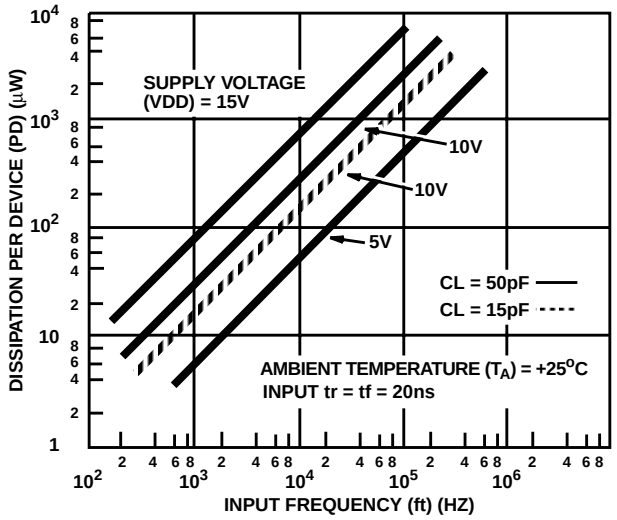
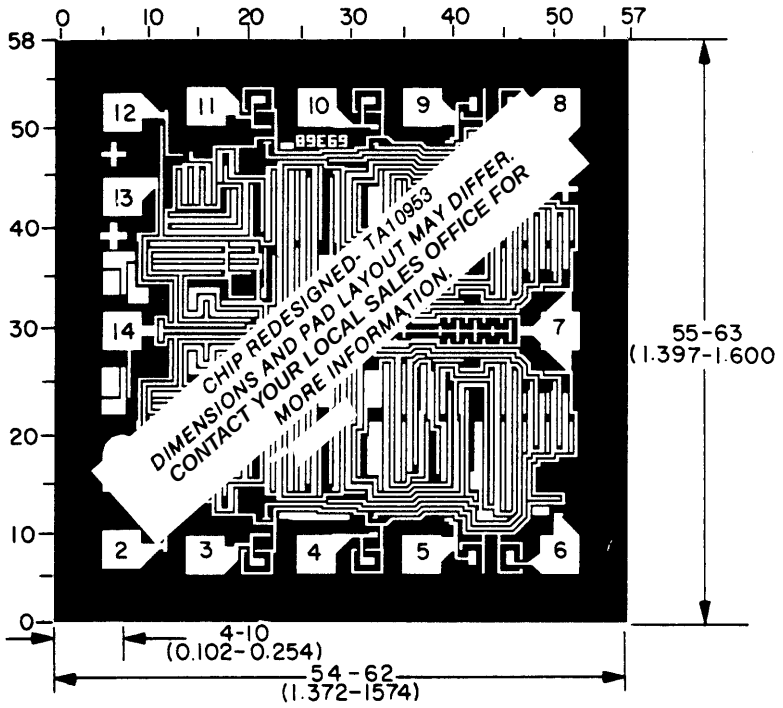


FIGURE 9. TYPICAL POWER DISSIPATION vs FREQUENCY

Chip Dimensions and Pad Layout



Dimension in parenthesis are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

METALLIZATION: Thickness: 11kÅ – 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

BOND PADS: 0.004 inches X 0.004 inches MIN

DIE THICKNESS: 0.0198 inches - 0.0218 inches

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